

Supporting information

Monolayer Graphene Terahertz Detector Integrated with Artificial Microstructure

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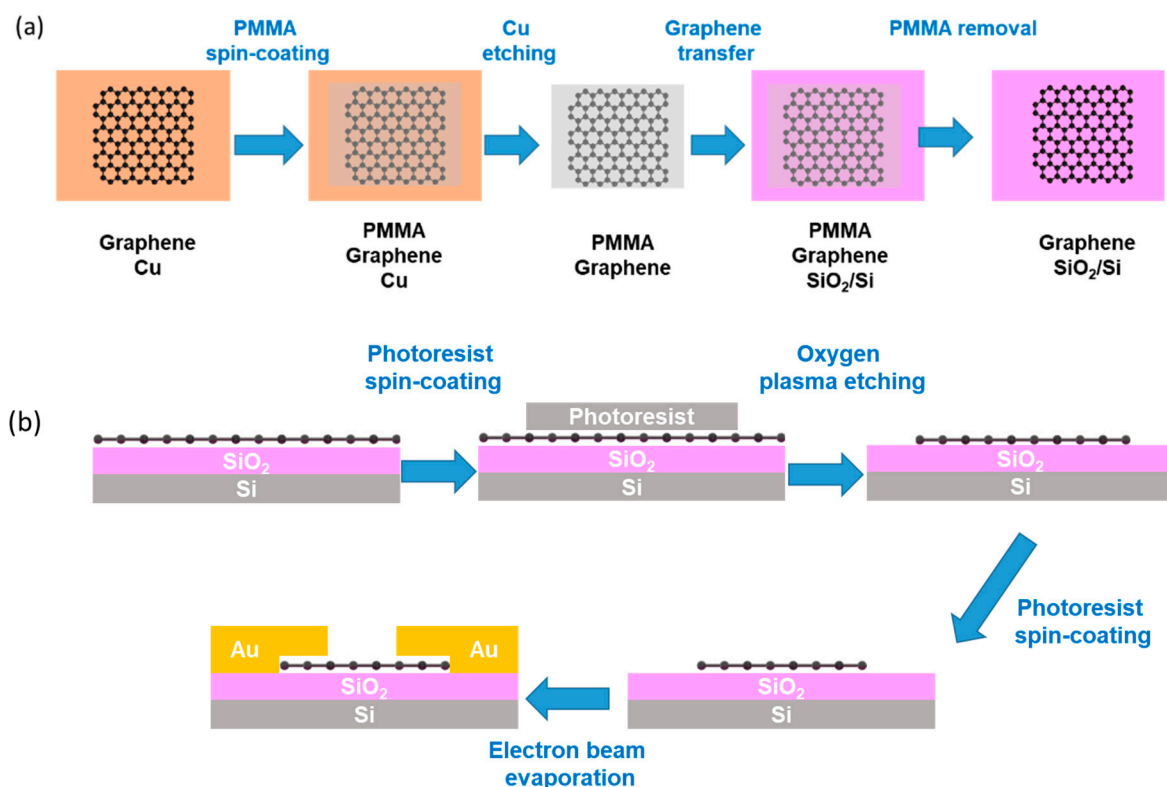


Figure S1. (a) Monolayer graphene transfer process (b) Monolayer graphene terahertz detector preparation process.

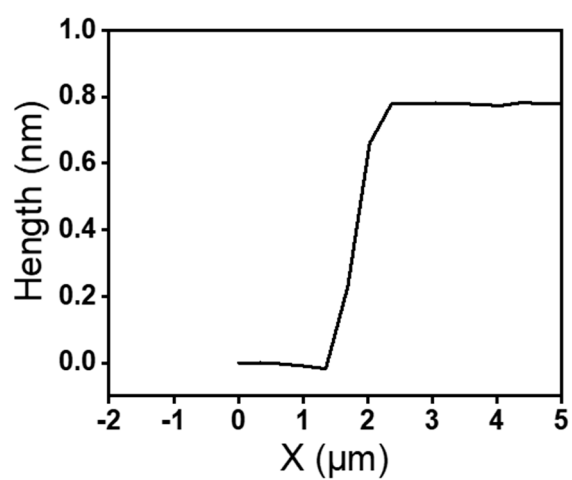


Figure S2. Height profile of the monolayer graphene tested by AFM.

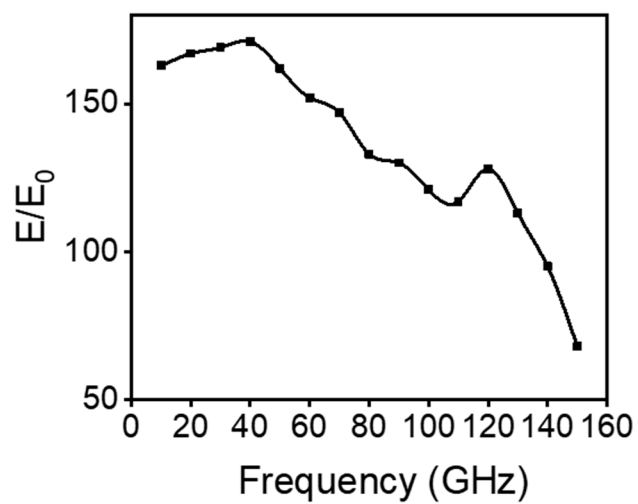


Figure S3. The antenna is characterised in the terahertz domain.